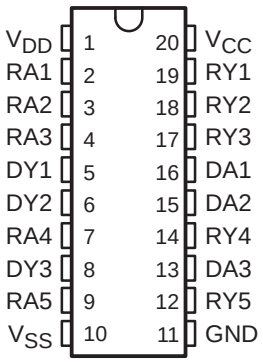
SLLS206C – MAY 1995 – REVISED JULY 1998

- **Single Chip With Easy Interface Between UART and Serial-Port Connector of IBM™ PC/AT™ and Compatibles**
- **Meets or Exceeds the Requirements of ANSI Standard TIA/EIA-232-F and ITU Recommendation V.28**
- **Designed to Support Data Rates up to 120 kbit/s**
- **Pinout Compatible With SN75C185 and SN75185**
- **ESD Protection to 2 kV on Bus Terminals**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB) Packages, and DIPs (N)**

DB, DW, OR N PACKAGE
(TOP VIEW)



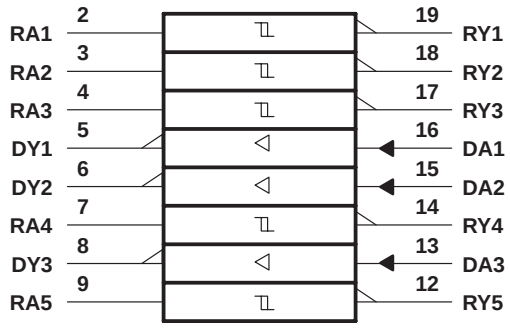
description

The GD75232 combines three drivers and five receivers from TI™ trade-standard SN75188 and SN75189 bipolar quadruple drivers and receivers, respectively. The pinout matches the flow-through design of the SN75C185 to decrease the part count, reduce the board space required, and allow easy interconnection of the UART and serial-port connector of an IBM™ PC/AT™ and compatibles. The bipolar circuits and processing of the GD75232 provide a rugged, low-cost solution for this function at the expense of quiescent power and external passive components relative to the SN75C185.

The GD75232 complies with the requirements of the TIA/EIA-232-F and ITU (formerly CCITT) V.28 standards. These standards are for data interchange between a host computer and a peripheral at signaling rates up to 20 kbit/s. The switching speeds of the GD75232 are fast enough to support rates up to 120 kbit/s with lower capacitive loads (shorter cables). Interoperability at the higher signaling rates cannot be expected unless the designer has design control of the cable and the interface circuits at both ends. For interoperability at signaling rates up to 120 kbit/s, use of ANSI TIA/EIA-423-B (ITU V.10) and TIA/EIA-422-B (ITU V.11) standards is recommended.

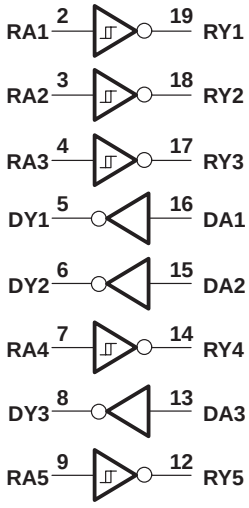
The GD75232 is characterized for operation over the temperature range of 0°C to 70°C.

logic symbol†

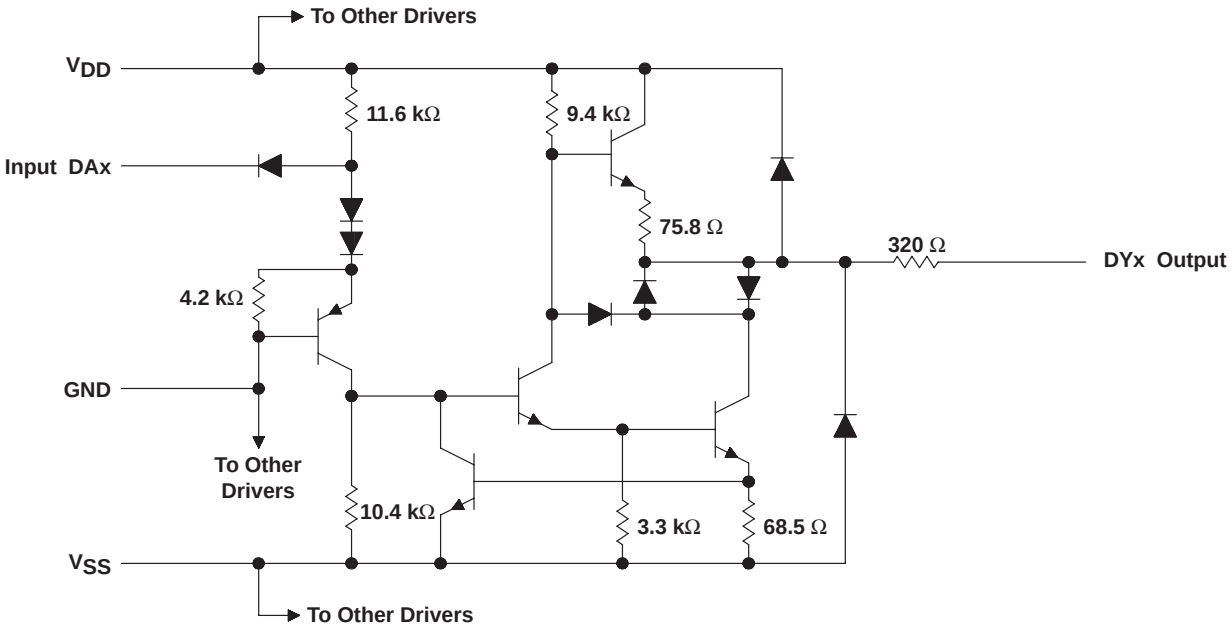


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)

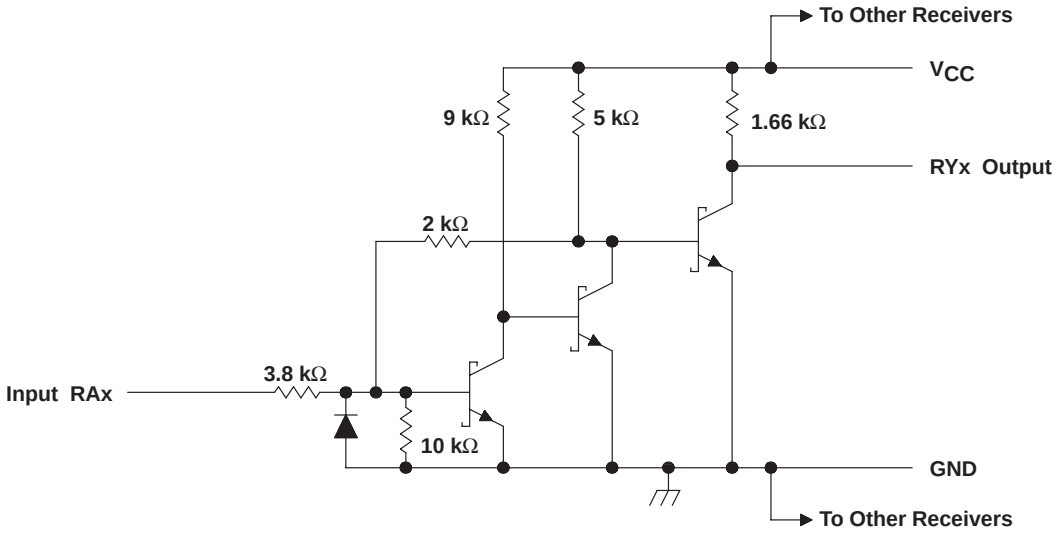


schematic (each driver)



Resistor values shown are nominal.

schematic (each receiver)



Resistor values shown are nominal.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{CC} (see Note 1) . . . . . 10 V
Supply voltage, V_{DD} (see Note 1) . . . . . 15 V
Supply voltage, V_{SS} (see Note 1) . . . . . –15 V
Input voltage range, V_I: Driver . . . . . –15 V to 7 V
Receiver . . . . . –30 V to 30 V
Driver output voltage range, V_O . . . . . –15 V to 15 V
Receiver low-level output current, I_{OL} . . . . . 20 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
N package . . . . . 67°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to the network ground terminal.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V_{DD}		7.5	9	15	V
Supply voltage, V_{SS}		–7.5	–9	–15	V
Supply voltage, V_{CC}		4.5	5	5.5	V
High-level input voltage, V_{IH} (driver only)		1.9			V
Low-level input voltage, V_{IL} (driver only)				0.8	V
High-level output current, I_{OH}	Driver			–6	mA
	Receiver			–0.5	
Low-level output current, I_{OL}	Driver			6	mA
	Receiver			16	
Operating free-air temperature, T_A		0		70	°C

supply currents over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS			MIN	MAX	UNIT
I_{DD}	Supply current from V_{DD}	All inputs at 1.9 V,	No load	V_{DD} = 9 V, V_{SS} = –9 V		15	mA
				V_{DD} = 12 V, V_{SS} = –12 V		19	
				V_{DD} = 15 V, V_{SS} = –15 V		25	
		All inputs at 0.8 V,	No load	V_{DD} = 9 V, V_{SS} = –9 V		4.5	mA
				V_{DD} = 12 V, V_{SS} = –12 V		5.5	
				V_{DD} = 15 V, V_{SS} = –15 V		9	
I_{SS}	Supply current from V_{SS}	All inputs at 1.9 V,	No load	V_{DD} = 9 V, V_{SS} = –9 V		–15	mA
				V_{DD} = 12 V, V_{SS} = –12 V		–19	
				V_{DD} = 15 V, V_{SS} = –15 V		–25	
		All inputs at 0.8 V,	No load	V_{DD} = 9 V, V_{SS} = –9 V		–3.2	mA
				V_{DD} = 12 V, V_{SS} = –12 V		–3.2	
				V_{DD} = 15 V, V_{SS} = –15 V		–3.2	
I_{CC}	Supply current from V_{CC}	V_{CC} = 5 V,	All inputs at 5,	No load		30	mA

DRIVER SECTION

electrical characteristics over recommended operating free-air temperature range, V_{DD} = 9 V, V_{SS} = −9 V, V_{CC} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	V_{IL} = 0.8 V,	R_L = 3 kΩ,	See Figure 1	6	7.5		V
V_{OL}	Low-level output voltage (see Note 3)	V_{IH} = 1.9 V,	R_L = 3 kΩ,	See Figure 1		−7.5	−6	V
I_{IH}	High-level input current	V_I = 5 V,	See Figure 2				10	μA
I_{IL}	Low-level input current	V_I = 0,	See Figure 2				−1.6	mA
$I_{OS(H)}$	High-level short-circuit output current (see Note 4)	V_{IL} = 0.8 V,	V_O = 0,	See Figure 1	−4.5	−12	−19.5	mA
$I_{OS(L)}$	Low-level short-circuit output current	V_{IH} = 2 V,	V_O = 0,	See Figure 1	4.5	12	19.5	mA
r_O	Output resistance (see Note 5)	V_{CC} = V_{DD} = V_{SS} = 0,	V_O = −2 V to 2 V		300			Ω

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only (e.g., if −10 V is maximum, the typical value is a more negative voltage).
4. Output short-circuit conditions must maintain the total power dissipation below absolute maximum ratings.
5. Test conditions are those specified by TIA/EIA-232-F and as listed above.

switching characteristics, V_{CC} = 5 V, V_{DD} = 12 V, V_{SS} = −12 V, T_A = 25°C

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	R_L = 3 kΩ to 7 kΩ,	C_L = 15 pF,	See Figure 3		315	500	ns
t_{PHL}	Propagation delay time, high- to low-level output					75	175	ns
t_{TLH}	Transition time, low- to high-level output	R_L = 3 kΩ to 7 kΩ,	C_L = 15 pF,	See Figure 3		60	100	ns
		R_L = 3 kΩ to 7 kΩ,	C_L = 2500 pF,	See Figure 3 and Note 6		1.7	2.5	μs
t_{THL}	Transition time, high- to low-level output	R_L = 3 kΩ to 7 kΩ,	C_L = 15 pF,	See Figure 3		40	75	ns
		R_L = 3 kΩ to 7 kΩ,	C_L = 2500 pF,	See Figure 3 and Note 6		1.5	2.5	μs

NOTE 6: Measured between ± 3-V and ± 3-V points of the output waveform (TIA/EIA-232-F conditions), all unused inputs are tied either high or low.

RECEIVER SECTION

electrical characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	See Figure 5	T_A = 25°C	1.75	1.9	2.3	V
			T_A = 0°C to 70 °C	1.55		2.3	
V_{IT-}	Negative-going input threshold voltage			0.75	0.97	1.25	
V_{hys}	Input hysteresis voltage ($V_{IT+} - V_{IT-}$)			0.5			
V_{OH}	High-level output voltage	I_{OH} = –0.5 mA	V_{IH} = 0.75 V	2.6	4	5	V
			Inputs open	2.6			
V_{OL}	Low-level input voltage	I_{OL} = 10 mA,	V_I = 3 V		0.2	0.45	V
I_{IH}	High-level input current	V_I = 25 V,	See Figure 5	3.6		8.3	mA
		V_I = 3 V,	See Figure 5	0.43			
I_{IL}	Low-level output current	V_I = –25 V,	See Figure 5	–3.6		–8.3	mA
		V_I = –3 V,	See Figure 5	–0.43			
I_{OS}	Short-circuit output current	See Figure 4			–3.4	–12	mA

† All typical values are at T_A = 25°C, V_{CC} = 5 V, V_{DD} = 9 V, and V_{SS} = –9 V.

switching characteristics, V_{CC} = 5 V, V_{DD} = 12 V, V_{SS} = –12 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 50 pF, See Figure 6	R_L = 5 kΩ,		107	250	ns
t_{PHL}	Propagation delay time, high- to low-level output				42	150	ns
t_{TLH}	Transition time, low- to high-level output				175	350	ns
t_{THL}	Transition time, high- to low-level output				16	60	ns
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 15 pF, See Figure 6	R_L = 1.5 kΩ,		100	160	ns
t_{PHL}	Propagation delay time, high- to low-level output				60	100	ns
t_{TLH}	Transition time, low- to high-level output				90	175	ns
t_{THL}	Transition time, high- to low-level output				15	50	ns

PARAMETER MEASUREMENT INFORMATION

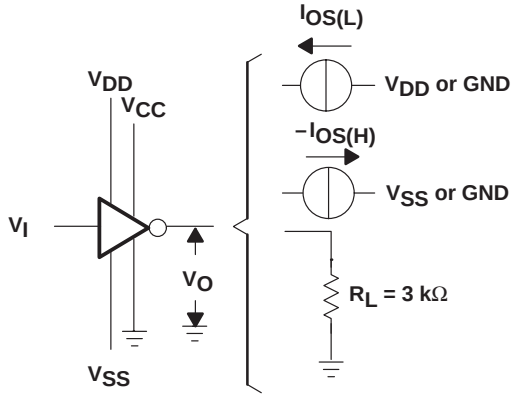


Figure 1. Driver Test Circuit for V_{OH}, V_{OL}, $I_{OS(H)}$, and $I_{OS(L)}$

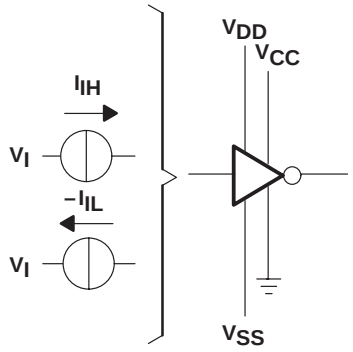
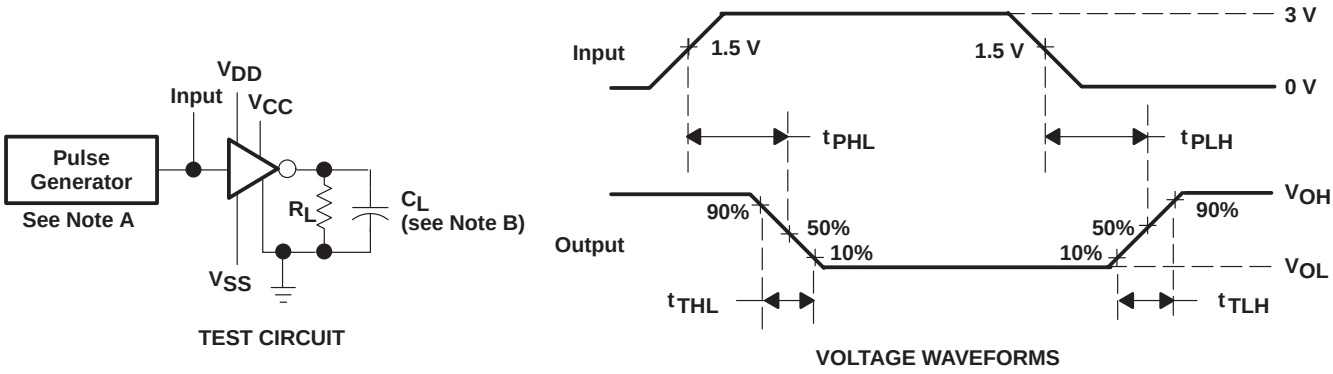


Figure 2. Driver Test Circuit for I_{IH} and I_{IL}



NOTES: A. The pulse generator has the following characteristics: t_W = 25 µs, PRR = 20 kHz, Z_O = 50 Ω, $t_r = t_f$ < 50 ns.
B. C_L includes probe and jig capacitance.

Figure 3. Driver Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

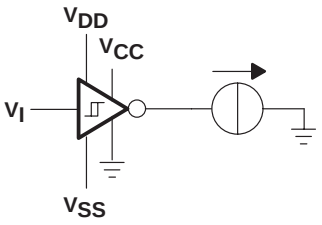


Figure 4. Receiver Test Circuit for I_{OS}

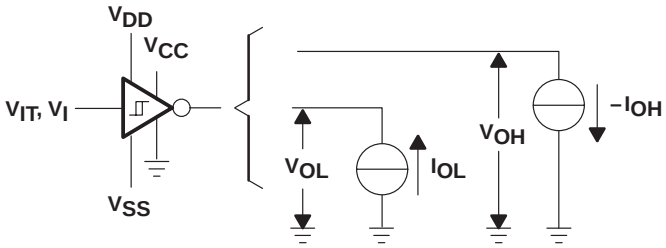
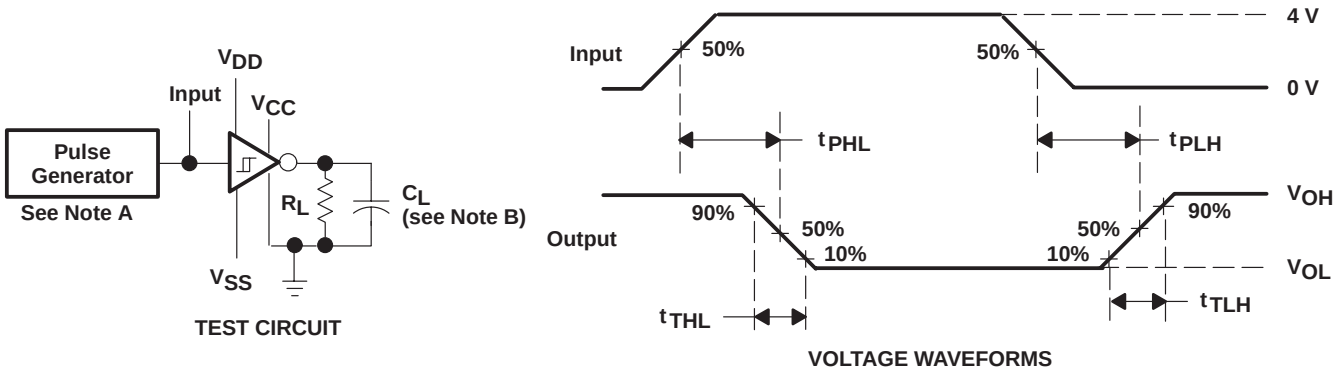


Figure 5. Receiver Test Circuit for V_{IT}, V_{OH}, and V_{OL}



NOTES: A. The pulse generator has the following characteristics: t_w = 25 μs, PRR = 20 kHz, Z_O = 50 Ω, $t_r = t_f$ < 50 ns.
B. C_L includes probe and jig capacitance.

Figure 6. Receiver Propagation and Transition Times

TYPICAL CHARACTERISTICS

DRIVER SECTION

VOLTAGE TRANSFER CHARACTERISTICS

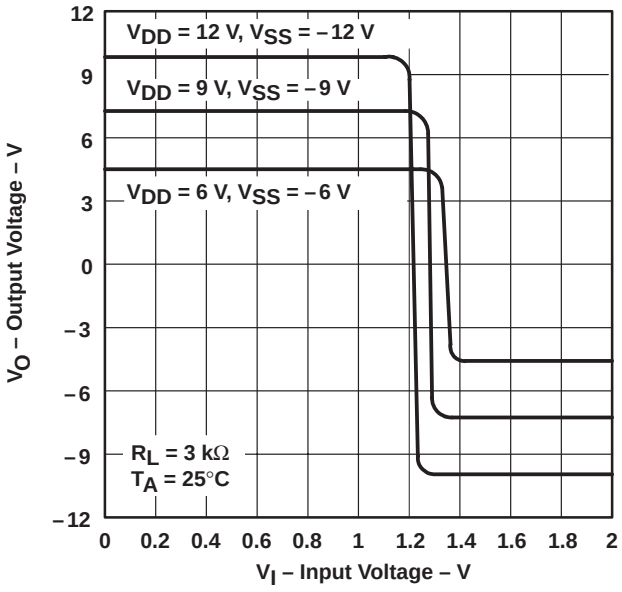


Figure 7

OUTPUT CURRENT vs OUTPUT VOLTAGE

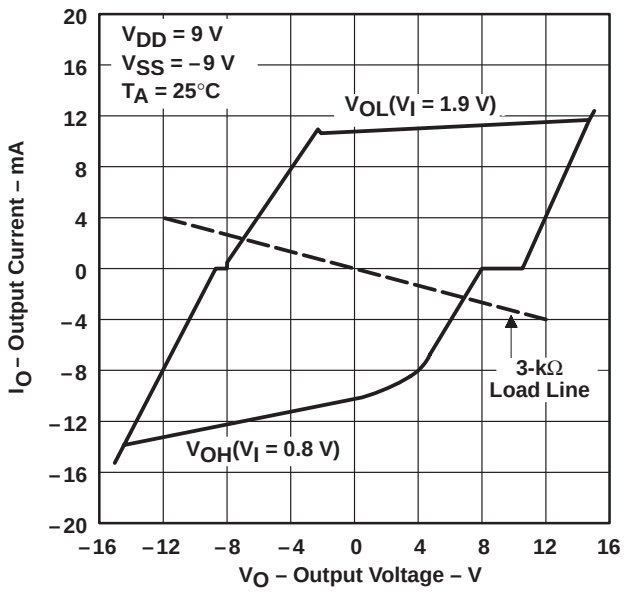


Figure 8

SHORT-CIRCUIT OUTPUT CURRENT vs FREE-AIR TEMPERATURE

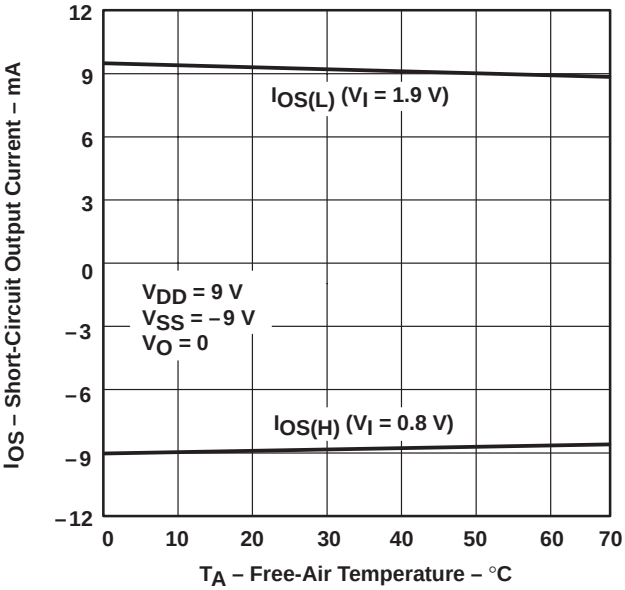


Figure 9

SLEW RATE vs LOAD CAPACITANCE

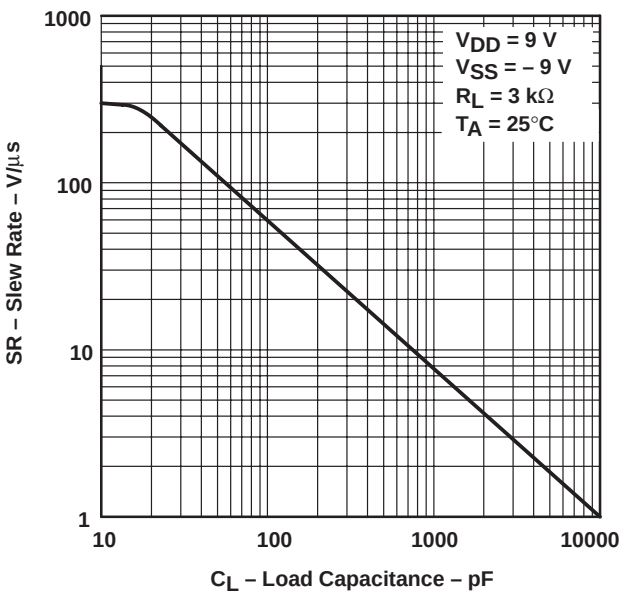


Figure 10

TYPICAL CHARACTERISTICS

INPUT THRESHOLD VOLTAGE vs FREE-AIR TEMPERATURE

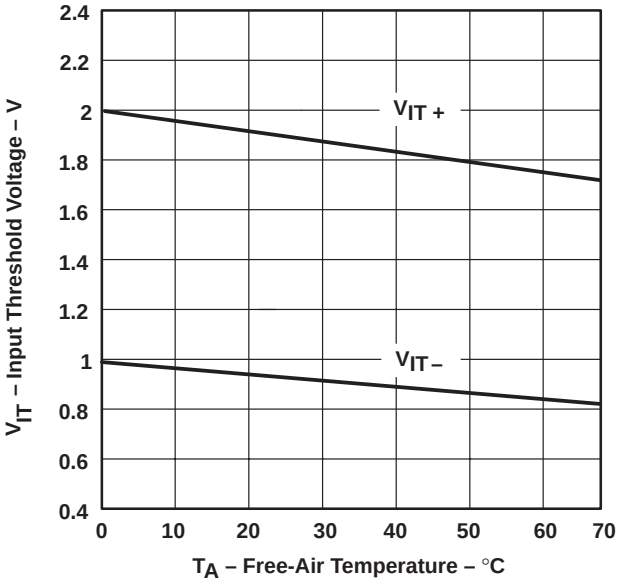


Figure 11

INPUT THRESHOLD VOLTAGE vs SUPPLY VOLTAGE

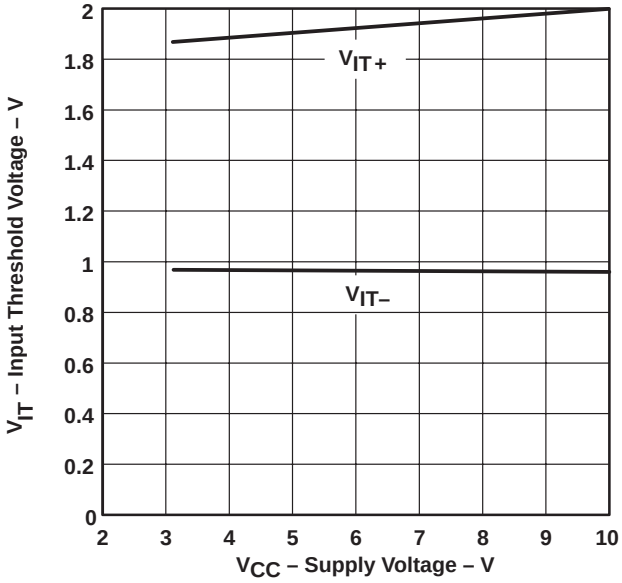
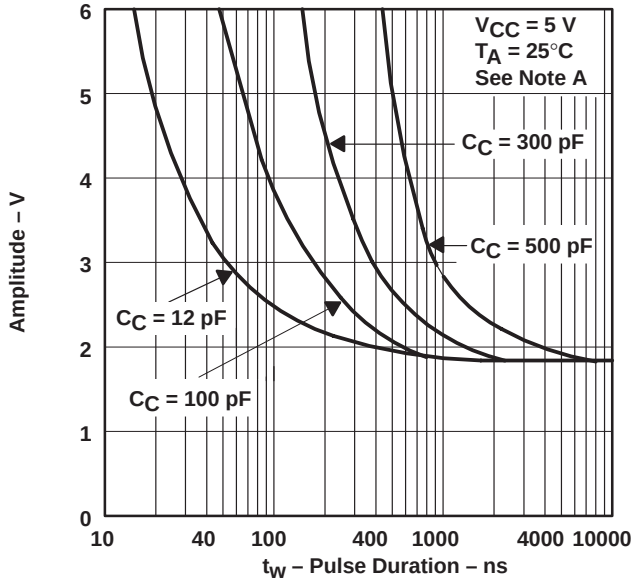


Figure 12

NOISE REJECTION



NOTE A: This figure shows the maximum amplitude of a positive-going pulse that, starting from 0 V, does not cause a change of the output level.

Figure 13

MAXIMUM SUPPLY VOLTAGE vs FREE-AIR TEMPERATURE

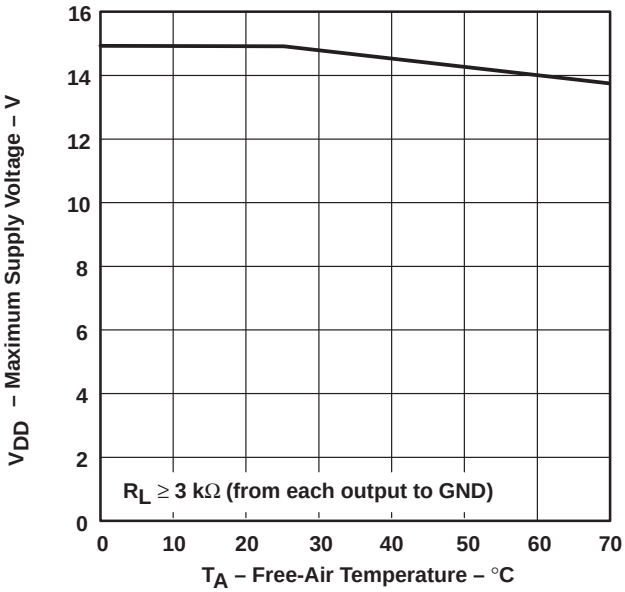


Figure 14

APPLICATION INFORMATION

Diodes placed in series with the V_{DD} and V_{SS} leads protect the GD75232 in the fault condition in which the device outputs are shorted to ±15 V and the power supplies are at low and provide low-impedance paths to ground (see Figure 15).

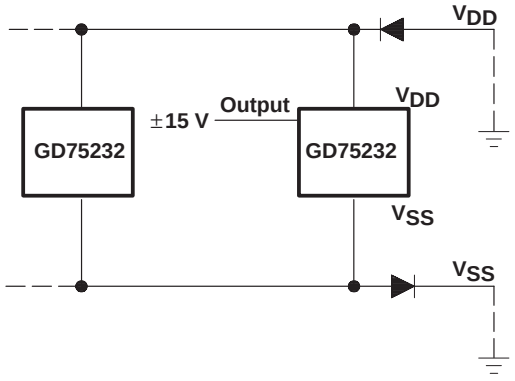


Figure 15. Power-Supply Protection to Meet Power-Off Fault Conditions of TIA/EIA-232-F

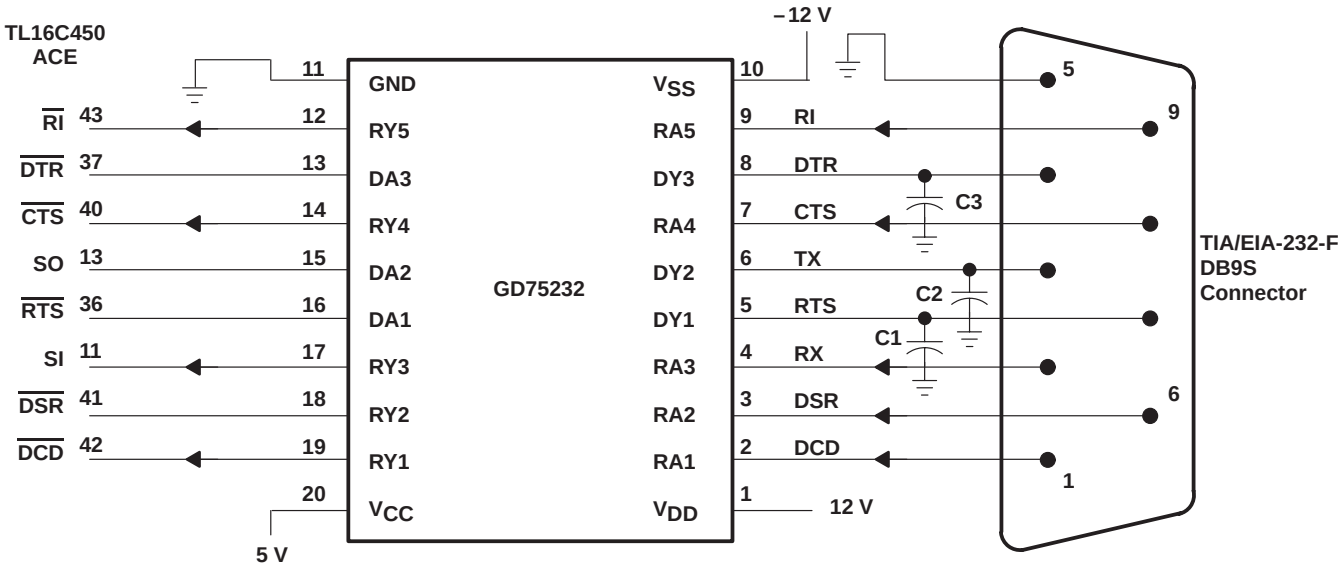


Figure 16. Typical Connection

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